

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	5 A
V_{RRM}	25 V
$T_j \text{ (max)}$	150°C
$V_F \text{ (max)}$	0.35 V

FEATURES AND BENEFITS

- VERY LOW FORWARD VOLTAGE DROP FOR LESS POWER DISSIPATION AND REDUCED HEATSINK
- OPTIMIZED CONDUCTION/REVERSE LOSSES TRADE-OFF WHICH MEANS THE HIGHEST EFFICIENCY IN THE APPLICATIONS
- HIGH POWER SURFACE MOUNT MINIATURE PACKAGE
- AVALANCHE RATED

DESCRIPTION

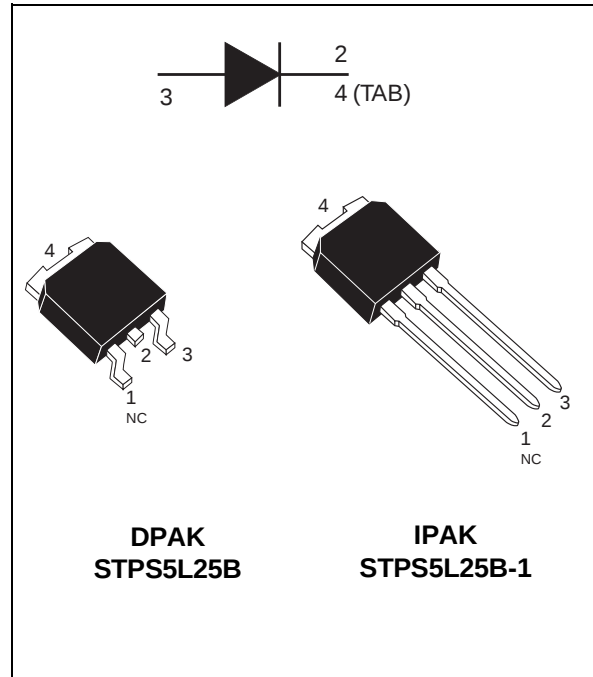
Single Schottky rectifier suited to Switched Mode Power Supplies and high frequency DC to DC converters.

This device is especially intended for use as a Rectifier at the secondary of 3.3V SMPS units.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		25	V
$I_{F(RMS)}$	RMS forward current		7	A
$I_{F(AV)}$	Average forward current	$T_c = 145^\circ\text{C} \quad \delta = 0.5$	5	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms Sinusoidal}$	75	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2 \mu\text{s square } F=1\text{kHz}$	1	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100 \mu\text{s square}$	2	A
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum operating junction temperature *		150	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink



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THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.5	$^{\circ}C/W$

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions	Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}C$	$V_R = V_{RRM}$		350	μA
		$T_j = 125^{\circ}C$		55	115	mA
V_F^*	Forward voltage drop	$T_j = 25^{\circ}C$	$I_F = 5\text{ A}$		0.47	V
		$T_j = 125^{\circ}C$	$I_F = 5\text{ A}$	0.31	0.35	
		$T_j = 25^{\circ}C$	$I_F = 10\text{ A}$		0.59	
		$T_j = 125^{\circ}C$	$I_F = 10\text{ A}$	0.41	0.50	

Pulse test : * $t_p = 380\text{ }\mu s$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :
 $P = 0.2 \times I_{F(AV)} + 0.030 I_F^2(RMS)$

Fig. 1: Average forward power dissipation versus average forward current.

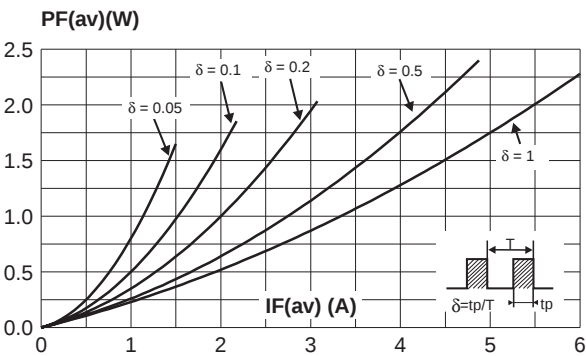


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

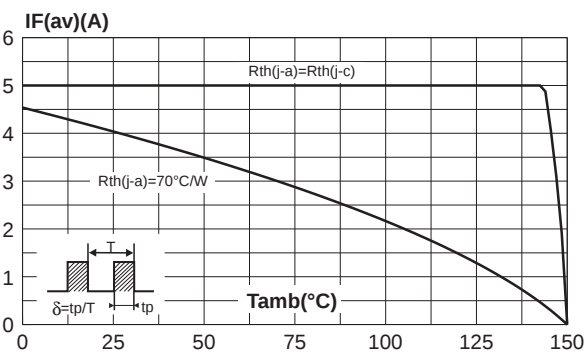


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values).

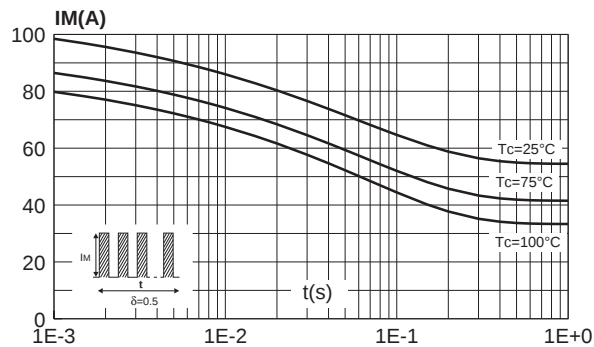


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration.

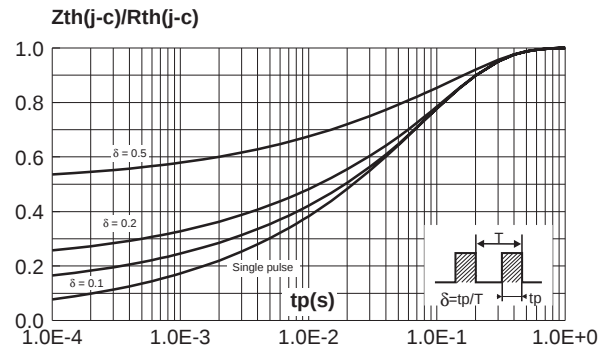


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values).

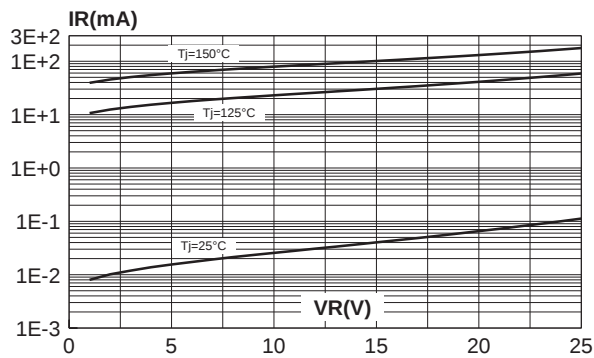


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

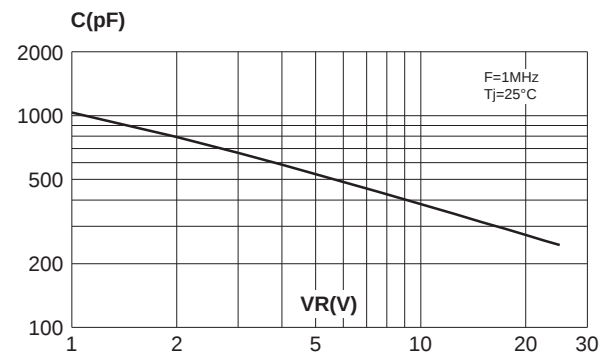


Fig. 7: Forward voltage drop versus forward current (maximum values).

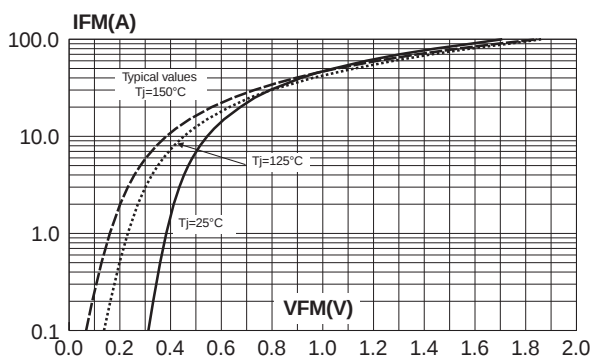
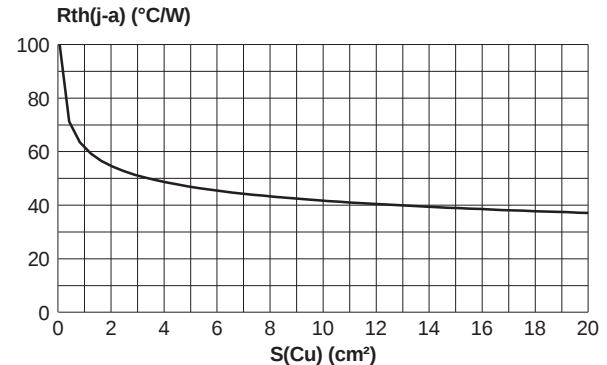
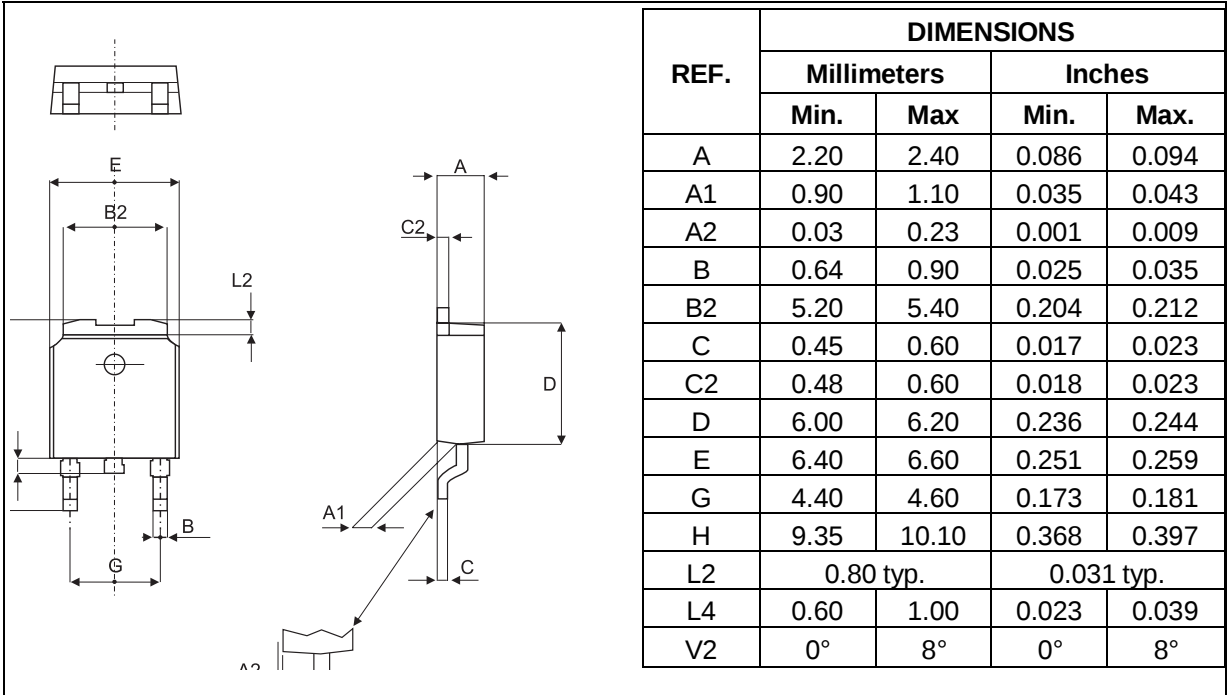


Fig. 8: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: $35\mu\text{m}$).

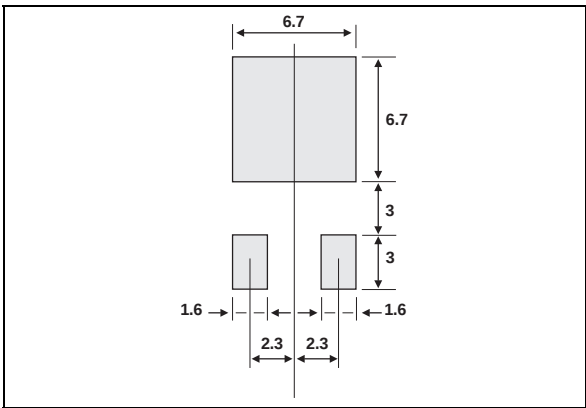


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PACKAGE MECHANICAL DATA
DPAK



FOOT PRINT DIMENSIONS (in millimeters)



PACKAGE MECHANICAL DATA
IPAK

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.035	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039
V1		10°			10°	

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS5L25B	STPS5L25B	DPAK	0.30g	75	Tube
STPS15LB-TR	STPS5L25B	DPAK	0.30g	2500	Tape & reel
STPS5L25B-1	STPS5L25B	IPAK	0.35g	75	Tube

■ Epoxy meets UL94,V0

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